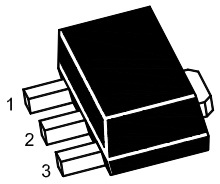
2SB1561SQ
PNP Transistor

SOT-89

Features

- Low collector saturation voltage
- Excellent h_{FE} characteristics



1. Base 2. Collector 3.Emitter
Marking : 1561

Absolute Maximum Ratings (T_a = 25℃)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	60	V
Collector Emitter Voltage	$-V_{CEO}$	60	V
Emitter Base Voltage	$-V_{EBO}$	6	V
Collector Current - DC Collector Current - Pulse	$-I_C$ $-I_{CP}$	2 6	A
Collector Power Dissipation	P_C	0.5	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	- 55 to + 150	℃

Characteristics at T_a = 25℃

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}$ = 2 V, $-I_C$ = 500 mA at $-V_{CE}$ = 2 V, $-I_C$ = 1.5 A	h_{FE}	120 45	- -	270 -	- -
Collector Base Cutoff Current at $-V_{CB}$ = 50 V	$-I_{CBO}$	-	-	100	nA
Emitter Base Cutoff Current at $-V_{EB}$ = 5 V	$-I_{EBO}$	-	-	100	nA
Collector Base Breakdown Voltage at $-I_C$ = 50 μA	$-V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at $-I_C$ = 1 mA	$-V_{(BR)CEO}$	60	-	-	V
Emitter Base Breakdown Voltage at $-I_E$ = 50 μA	$-V_{(BR)EBO}$	6	-	-	V
Collector Emitter Saturation Voltage at $-I_C$ = 1 A, $-I_B$ = 50 mA	$-V_{CE(sat)}$	-	-	0.35	V
Transition Frequency at $-V_{CE}$ = 2 V, I_E = 0.5 A, f = 100 MHz	f_T	-	200	-	MHz
Output Capacitance at $-V_{CB}$ = 10 V, I_E = 0, f = 1 MHz	C_{ob}	-	23	-	pF

Typical Characteristics Curves

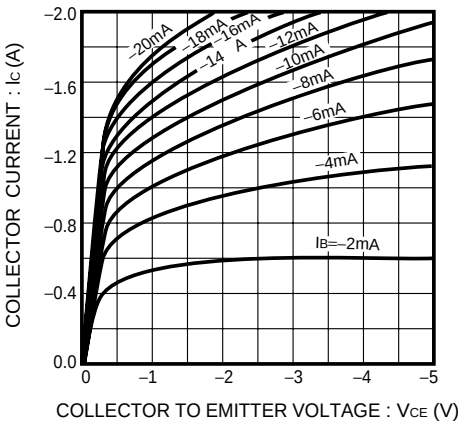


Fig.1 Grounded emitter output characteristics

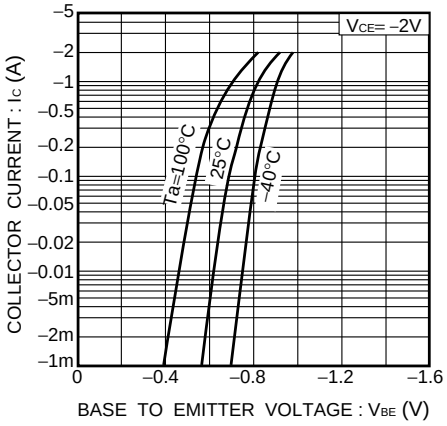


Fig.2 Grounded emitter propagation characteristics

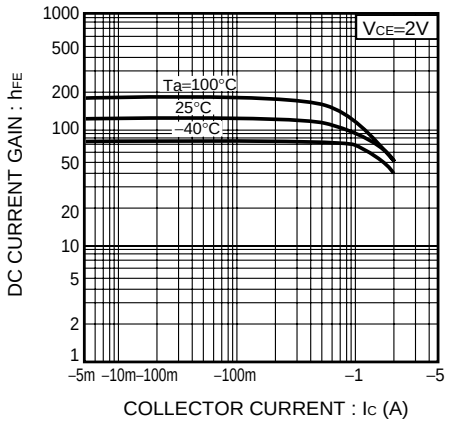


Fig.3 DC current gain vs. collector current (I)

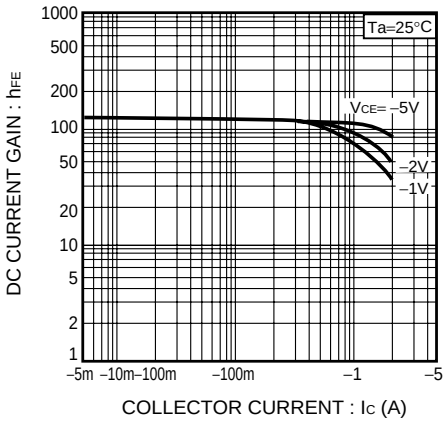


Fig.4 DC current gain vs. collector current (II)

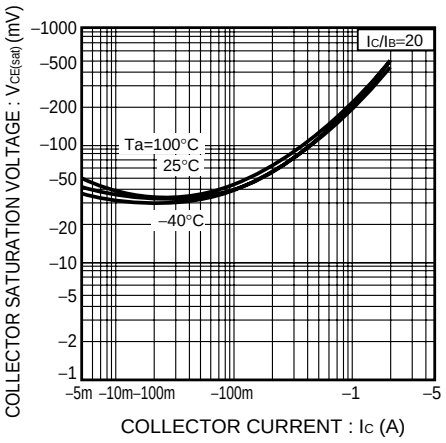


Fig.5 Collector-emitter saturation voltage vs. collector current (I)

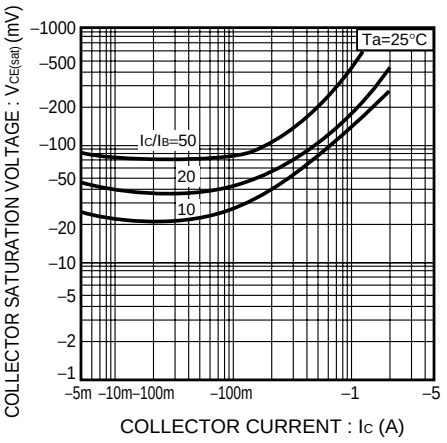
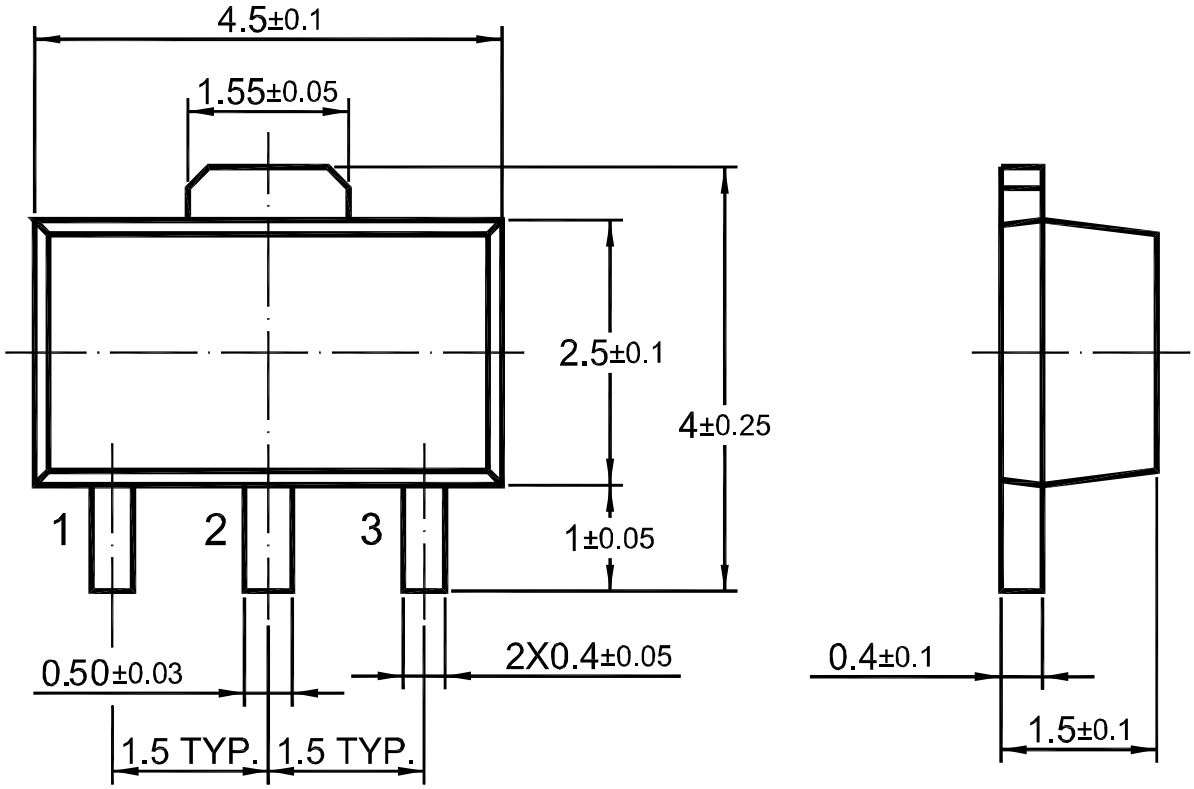


Fig.6 Collector-emitter saturation voltage vs. collector current (II)

Package Outline

SOT-89
Dimensions in mm



Ordering information

Device	Package	Shipping
2SB1561SQ	SOT-89	1000/Tape&Reel(7inches)